EXHIBIT A

U.S. SERIAL NO.: 10/521,619

ASSIGNMENT OF PATENTS

This Assignment of Patents (this "Assignment") is effective as of the Initial Closing Date (as defined in the Asset Purchase Agreement (the "Asset Purchase Agreement"), dated as of October 10, 2003, by and among ASML Holding N.V., a Dutch company ("Parent"), ASML U.S., Inc., a Delaware corporation and a wholly-owned subsidiary of Parent ("Seller U.S."), and the other affiliates of Seller U.S. party thereto (together with all of the foregoing parties, each a "Seller" and collectively the "Sellers"), on the one hand, and Thermal Acquisition Corp., a Delaware corporation ("Buyer")). Capitalized terms used herein but not defined shall have the meanings ascribed to such terms in the Asset Purchase Agreement.

WHEREAS, upon the terms and subject to the conditions in the Asset Purchase Agreement, Sellers have agreed to assign and transfer to Buyer, among other things, certain Patents (as defined below);

WHRRAS, in order to further effect the assignment and transfer of such Patents, Buyer has requested that Seller U.S. execute and deliver to Buyer this Assignment;

NOW, THEREFORE, for good and valuable consideration, the receipt and sufficiency of which is hereby acknowledged:

1. Sellers agree to and hereby do assign, sell, transfer, grant and convey to Buyer, its successors and assigns, all of Sellers' worldwide right, title and interest in and to all Patents listed on schedule 3.18(a)(i) of the Disclosure Schedule and all causes of action, demands, judgments, claims, or other similar rights of Sellers relating primarily to such Patents.

"Patents" shall mean all U.S. and foreign patents and applications therefor and all reissues, divisions, renewals, extensions, provisionals, continuations and continuations-in-part thereof.

- 2. Sellers authorize and request the United States Patent and Trademark Office and head of any foreign patent office to issue all patent registrations which may issue on any applications for any Patents to Buyer, its successors and assigns, in accordance with this Assignment.
- 3. Promptly upon the request of Buyer, Sellers shall execute such documents and perform such actions as may be necessary to perfect the assignment of rights contained in this Assignment.
- 4. Nothing herein shall affect, or be deemed to affect, the representations, warranties, covenants, and indemnities contained in the Asset Purchase Agreement.
- 5. This Assignment may be executed in one or more counterparts and signature may be delivered by facsimile, each of which shall be deemed an original, but all of which together shall constitute one and the same instrument.

IN WITNESS WHEREOF, Seller U.S. has caused this instrument to be executed by its duly authorized corporate officer as of the Closing Date:

ASML U.S., Inc.

By: .

Name: C. Douglas Marsh

Title: Vice President Business Integration

& U.S. Institutional Relations

ACKNOWLEDGED AND AGREED:

Thermal Acquisition Corp., a Delaware Corporation

By:

Name: Jerauld Cutini

Title: President and Chief Executive Officer

IN WITNESS WHEREOF, Seller U.S. has caused this instrument to be executed by its duly authorized corporate officer as of the Closing Date.

ASML U.S., Inc.

By:

Name: C. Douglas Marsh
Title: Vice President Business Integration
& U.S. Institutional Relations

ACKNOWLEDGED AND AGREED:

Thermal Acquisition Corp., a Delaware Corporation

By:

Name: Jerauld Cutini

Title: President and Chief Executive Officer

DISCLOSURE SCHEDULES SCHEDULE 3.18(a)(i)

The following Patents:

Attachment 1 to

Disclosure Schedule 3.18(a)(f)

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		ಕ	•	Title/Inventors			• .	
\	163.50				Seriel No.	Patrent No.	Kenter	Ė
ξ	201/8		<u> </u>	LOW TEMPERATURE CHEMICAL VAPOR	07/068.727	Issue Date	Countries	
FA	16178	ė.	A.T.	LOW TRAPERATURE CHEMICAL VAPOR	06/29/87	07/04/89		
⋖	16178	7	AST.	CVD REACTOR AND GAS INJECTION SYSTEMS	06/14/86	2134184 12/26/97	Japan	
FA	. 16178	7-JP	AJT	CVD REACTOR AND GAS INTECTION SYSTEM	1027/87	4,834,022 05/30/89		
∢	16178	∞ ·	<u>A</u>	FLUIDIZED BED HEATER FOR SEMICONDUCTOR PROCESSING	07/14/86 707262	2076448 · 08/09/96	Japan	
∢	40356		A5T	RAPID INFRARED CURING OF PHENOL PHENOLIC, EPOXY AND OTHER PRESSURE THE PROPERTY.		06/16/87		
∢	44048		AT	ATMOSPHERIC PRESSURE CHEMICAL VAPOR DEPOSITION APPARATUS AND METHOD/		4,834,020		
FA	44048	et .	AJŢ	ATMOSPHERIC PRESSURE CHEMICAL VAPOR DEPOSITION APPARATUS AND METHOD/	63-307653 17m5100	2930960	Japan	
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4	44521	-	AST	R IMPROVING THE STEP COVERAGE RIC IN VLSI CIRCUITS/Shamshoian		Abandoned 4,891,247		
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1	8	-	AT.	VAPOR DELIVERY SYSTEM		Intrae Date	Countries	
¢	23861		AJT .	CHEMICAL REFIT I SYSTEM	Closed			T
4	86598	8	- ITV	HRATHR WAY DE CONSTITUTE	Closed		-	
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FA.	\$6598	<u> </u>	#4.4	Simple State Comments	6-511396	Abandoned	Japan	T
			<u>i</u> ·	GAS HEATER FOR PROCESSING GASES/Colling	701790/95	162766		
田	26598	田	A-T	GAS HEATER FOR PROCESSING GASTES/C. H.	11/03/93	09/04/98	South Korea	
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				LEAFOR FRUCESSING GASES/Collins	PCI/U893/10532	Closed	PAT	Т
	12112		AJŢ	BPSG STABILITY ENHANCING CAP LAYER/	11/03/93			
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	300	2	<u> </u>	SUBSTRATE FOR A THIN DESCRIPTION OF GLASS	PCI/U894/01278	(A-59072-1)		,
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·			WES	DELIVERING GASES TO A SURFACE/Dedominey	08/276,815	Abendoned in favor		
FA	59471	ar e	ACT	DY INJECTOR FOR DELLYBRING GASTES		(A-59471-1)		
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₹_	62732	1	15	TVE GAS SHIRLD FOR CHRACAT THE	02/13/97	(A-62732-1)	
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	ThickInventors	DIPOSITION	OPTEMIZING SIO2 FILM CONFORMALITY IN	DPITMIZATION OF STANDS	ATMOSPHERIC PRESSURE CHEMICAL VAPOR DEPOSITION	LOW K DIRLECTRICS PREPARED FROM	CROSS-LINKED PPXS (CL.PPXS)/LA	DIBLECTRICLO	A METHOD OF FLANARIZING A DIELECTRIC LAYER WITH REDUCED HYDROGEN DIFFUSION/ Hakin	LOW. K DIELECTRICS PREPARED FROM PECYD	HIGH TEMPERATURE ROLLER MONTH BIRL	Mericon non non-	EMBEDDED LOW R MATERIAL SP.,	OPTIMIZATION OF SIO, FILM CONFORMITY	INATION REDUCTION BY.		ON OF ALL OXIDE SURFACE	MINATION REDUCTION BY OXIDE STIRFACT	·		
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63665	288	12	METHOD OF CONTAMINATION PERFORMANCE	13/06/98		
63665	- 1	SQ A	FORMATION OF ALL OXIDE SURFACE LAYERS/Beiley, Brady	9904262-4	67703 1024/00	Singapore
·		NESS .	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE	87102978 03.07.08	147013	Taiwan
63665	Bi .	ATT	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE	98910258.7 03/06/08	04/13/02	Burope
3665	Ž	A5T MSS	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE	PCT/US98/04570	Closed	. 5
63959	·	AGS MSS	FLANGE CLAMPMatbox, Kamian	087746 600		
63969	2	ATT		11/13/96 PCT//13/97/201216	Abandoned	
63672		AT		11/06/97	Anendoned	R CT
63673		15 M	Sermen, Elbal	08/796,300	Closed 5,921,560	
63674		15 × 5	INTECTION SEAL/Miller, Veeck	<i>UZJUT/97</i>	07/13/99	•
63675.	1.		CAI		Closed	
63676		A P	CONDITION SYSTEMS/Moshingh CONDITIONING TOWER/Kleiner	04/14/97	5,938, <u>8</u> 51 08/17/99	
63677			ochtagh	02/05/98 Closed	Abendoned.	
64309	7 6	ASS MSS				
64725		AST	$\neg \tau$		Combined with A. 59471-3 and closed	
463	I-71935/MSS (463635-828)		7	Closed		

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Title/Inventors	FLAT FLATE DISCHARGE CHIL OZONE	GENERATORS/Grandos	APPARATUS FOR PROCESSING A SEMICONDICTOR STREETS AT SEMICONDUCTOR	WAFER CARRIER AND STATICONTINUES	APPARATUS FOR PROCESSING A	MEMICONDUCTOR SUBSTRATE/Yao, Bailey	WAPER CARRIER AND SPACES WITH	APPARATUS FOR PROCESSING A SEMICONDITIONS STREETS ATTER	WAFIR CARRIER AND OFFICE	APPARATUS FOR PROCESSING A SEMICONDICTOR	WAFER CARRIED AND STRAIGHT	APPARATUS FOR PROCESSING A SEMICONDITION STREET, AMERICAN	WAFER CARRIER AND SPACES MAN	APPARATUS FOR PROCESSING A SEMICONDUCTOR SUBSTRATEVAL DESIGNATION OF THE STRATE A T	WAFER CARRIER AND SEMICONDUCTOR	AFFARATUS FOR PROCESSING A SEMICONDUCTOR STREETS ATTEXA	WAFER CARRIER AND SEMICONDUCTOR	AFFAKATUS FOR PROCESSING A SEMICONDUCTOR STREETS ATTERVALLE.	WAFER CARRIER AND SEMICONDIFICED	APPARATUS FOR PROCESSING A		The pariety		13 FOR PROCESSING A OCTOR STREETS A TENTO
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65583		ASS MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	09/185,180 11/03/98	6,056,824	
65583	3 1-PC	ATT	FREE FLOATING SHIELD AND SEMICONDUCTOR	CIP of 09/008,024 PCT/US98/25740	Closed	E
65583	1-CA	ASS ASS	FREE FLOATING SHIELD AND SEMICONDUCTOR	2318147		
65583	2	ASS MSS	DUCTOR	12/04/98 98813641.4	• • •	
65583.	闺	MSS	DUCTOR ody, Jry B.	12/04/98 . 01104322.0 06/21/01	Abendoned	Hong King
66583	Ej.	ATT	ATING SHEED AND SEMICONDUCTOR	98960728.8		
65583	迁	ASS MSS	DUCTOR	12/14/98 13/315.	Abendoned	adomina .
65583	7	ASS MSS	DUCTOR	12/04/98 2000-540285	3416114	Decorate de la constant de la consta
£8599	<u> </u>	AAT. MSS	DUCTOR	2000-7007859	346767	
65583	-SG	AST. MESS	ATING SHIRLD AND SEMICONDUCTOR	T	07/18/02	South Kanes
65583	1-TW	ATT	ATING SHIELD AND SEMICONDUCTOR	:	08/30/02	Singapore
65583	2	AJT	VING SHIELD AND SEMICONDUCTOR NG SYSTEM/Butholomew, et al.	*	10/27/01 6,352,592 B1	I siwan
65533	25.54	AST	DUCTOR	185,180	20 to 10	
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臣	£3559	3 2-10	44F	FREE FLOATING SHIELD AND SEALCONDICTOR	04/10/00		China	T
F.	285599	3 2世		PRER FLOATING SHIELD AND SEARCONDUCTOR	04/07/00		Burope	T
FA	65583	3 2.TE	ATT	DUCTOR	2000-108638	репорициу	Hong Kong	l
FA.	65583	2.KR	_		04/10/00.	338801	unda _f	
FA	8283	2-MY	AGS	DUCTOR	04/10/00 PI20001457	05/20/02	South Kores	
FA	65583	2-80	ATA	DUCTOR	04/07/00		Malaysia	
FA	68583	2-TW	AAT	DUCTOR	03/31/00 89106510		Singapore	
FA	66583	2-TH	ASS.	ATING SHIELD AND SEMICONDUCTOR	04/08/00	,	Taiwan	
¥	65816	<u> </u>	ATT. MSS	ANE DERIVATIVES CONTAINING VEING GROUPS/Golden	04/03/00 Hold .	Delitionary	Theiland	· .
4			AJT. MŠS	ORGANIC MAKING/Rose;	09/067,704 04/28/98	6,068,884 05/30/m		
FA .	99659	ઇ .	AJT. MSS	LECTRIC INORGANIC/ORGANIC EMS AND METHOD OF MAKINGROSE;	2,330,040	Abendoned	Canada	
FA	65965	Z	AJT. MESS		99806506.4 041.5/99		China	
		HK .	AST.	LECTRIC INORGANIC/ORGANIC MS AND METHOD OF MAKING/Rose;	9	Abundoned	Hong Kong	
FA	59659	日	AF	BCTRIC INORGANIC/ORGANIC				
;		1		AND METHOD OF MAKING Rose,	٠.	Authomed	larsei	

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		<u> </u>	MSS	LOW & DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKINGROSE; LOPATE: Felts	2000-545704 . 04/15/99		Japan	
	53659	X	ATT	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose;	2000-7012019		South Korea	- Ţ
 	65965	88	AJT	LOW K DIRLECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKINGROSS	200005999-8	76753	Singapore	``
十	59659	TW .	AT	Lopate; Relts LOW R DHH ECTET C PROPERTY		12/07/02	•	
		•	MESS	HYBRID FILMS AND METHOD OF MAKING/Rose; Lopate; Feits	88106881 04/28/99	161126 06/19/02	Taiwan	
•	65965		AJT. MESS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopsie: Felis	99917529.2· 04/15/99		Биторе	
		교	AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKINGROSE; Lopste. Polis	PCT/US99/08246 04/15/99	Closed	PCT	·
9	59659	ᅻ.	AJT	TECTRIC INORGANIC/ORGANIC LMS AND METHOD OF MAKING/Rose;	09/361,667 07/27/99			
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Ť		-	METHOD/Dobbin; Striffer, Modrogan				T
<u> </u>	65692	AT	WAFER PROCESSING REACTOR HAVING A GAS		•	•	
		45	FLOW CONTROL SYSTEM AND METHOD/ Burtholomeus	02/02/99	Closed .	-	T
9	65699	5	WAFER PROCESSING PRACTICE TAXES			·	
	-	MESS	FLOW CONTROL SYSTEM AND METHOD/ Bertholomer Reiber 7 2 2 2	09/493,492 01/28/00	6,143,080		_
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		WESS	FLOW CONTROL SYSTEM AND METHOD/ Bartholomew Beller Furth Paris Paris	2362694	Abendoned	Cenada	_
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	-	MSS	FLOW CONTROL SYSTEM AND METHOD/	00804644.1		China	·
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18	03039	SC T	FLOW. CONTROL SYSTEM AND METHOD	2000-599919		Japan	
-		Mess	WAFER PROCESSING REACTOR HAVING A GAS	2001-7009763			
8	9S 65699	5	WAFER PROCESSING REACTOR HAVING A CALC	02/01/00		South Korea	•
18	WT 65699	Z E	FLOW CONTROL SYSTEM AND METEOD	200104725-7 02/01/00		Singapore	
		MSS	A GAS	8910184K			
4	-	•	Belley: Runid: Rolling	02/02/00	,	Teiwan	
65669	월 왕	AT	CRISING REACTOR HAVING A GAS				
		2		02/21/00		Burape	
66692	<u>22</u>	AT	A GAS	Tigothacec			
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		_	MESS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND A CONTROL OF THE PROCESSION OF THE PROCE		Closed Date	Countries
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		•	MSS	GAS DELIVERY METERING TUBE/Stoddard; Yao;	60/135.358		
٧	67178	200	A5T	GAS DELIVERY METHRING TIME A	05/21/99		
¥.	67178	į g	MESS	Yao; Hamilton; Young; DeSa	09/470,446		
			MSS	AAS DELIVERY METHRING TUBE/Ingle; Stoddard;	2308758		
FA.	87178	₹ ∞	17	GAS DELIVERY METERING TUBE	05/18/00	Doublemon	Cemedia
	4		MSS	Yeo; Hamilton; Young, DeSa	00108583.2	ZL00108583.2	Chins
된 .	87.I78 	<u>出</u>	AT	GAS DELIVERY METERING TUREIngle: Studdismi-	00304100	05/21/03	·
M	67178	開	157	GAS DET HERE'S COMES DESA	05/78/00	***	Burope
•	_		MESS	Yac Hamilton: Vome. P.S.	01102509.9	Abendoned	
FA	67178	S. F.	¥.	GAS DELIVERY METERNA TERRA	04/10/01		Hong Kong
		_	SSE	Yao; Hamilton; Young: DeSa	2000-148939		The state of the s
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FA	67178	ZŽŽ	157	GAS DHI INTERS A AMERICAN	05/19/00		South Korea
	-		MESS	Yac Hamilton Venn P. C.	PI-20002163		
FA :	67178	SG	AJT.	GAS DELIVERY METERING TUBE/ingic, Stoddard:	200002705.2	·	Malayaia
FA	82179	門	AFT		06/16/00		Singapora
FA	87178	M	<u> </u>		05/18/00	Abandoned	Theiland
.			MSS		89106456	140755	
	67178	-	MESS	GAS DELIVERY METERING	04/07/00 Tinfil-1	01/09/02	Tarwan
	67178	-	AT	RY. METERING TUBE/DEDICATION DESCRIPTION OF STREET			
FA	87179	Z Z	MSS	RY METHENIC TITES / A	07/13/01	•	
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1			7	2002-0040745 ·		South Korea
770	V I-MY		GAS DELIVERY METERING TUBE/Authory Desa; Jay B. Dedoringy, Samuel Revite			Melonais
8L119	8 1-SG	MOV	G TUBE/Anthony Desa; Jay	200204131-7		C.
82179	WI-I 8	MESS	G TUBE/Anthony Desn; Jay	07/09/02 91115232		and done
67178	8 1:EP	Mass	VERY METERING TUBE/Dess; DeDominey;	07/09/02 02254962.0		Larwan
67388		ASS:		07/15/02 07/570,331	Abandoned	Somope .
	86. Edi.	AJT	POR DEPOSITING SILICON DIOXIDE PRODUCT/Mahawiii	06/22/89	2,918,300	Kepen
67388	žž	A7.	FOR DIPOSITING SII ZAMANA	06/22/90	04/23/99 Abandoned	
		NSS ·	PRODUCT/Mahawili	1990-9287 06/22/90	. 86/10/60 259/291	South Korea
67388	TW.	AJT MSS	METHOD FOR DEPOSITING SILICON DIOXIDE 75	79105124	Abendoned 50924 - 08.77 to 1	
67388	DB	AJT	OR DEPOSITING SILICON DIOXIDE	06/22/90 90111648:3	Abandoned 0404101	rawan T
67388	峊	ALT	OR DEPOSITING SILICON DIOXIDE	•	96/10/50	Germany
67388	展				05/01/96	Вигоро
67388	8		OR DEPOSITING SILICON DIOXIDE		96/10/50	France
67388	足		OR DEPOSITING SULCON DIOXIDE	·	0404101 05/01/96	Great Britain
67388	1		PRODUCT/Mahawiii	,	0404101 05/01/96 Abendoned	Notherlands
		MSS		02/27/91	Abendoned	

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	This/inventors	CHEMICAL VAPOR DEPOSITION REACTOR AND	CHRMICAL VAPOR DEBOSTRON BELLEVILLE	METHOD OF OPERATION/Mahawiii	CHEMICAL VAPOR DEPOSITION REACTOR AND METHOD OF OPER ATTOMACL	CHEMICAL VAPOR DEPOSITION REACTOR AND	CHEMICAL VAPOR DIRECTION BELONGED	METHOD OF OPERATION Makewill MULTI-ZONE PLANAR HEATER ASSESSMENT	METHOD OF OPERATION/Mahawiii	METHOD OF OFFRATION MARWIII	MULTI-ZONE PLANAR HEATER ASSEMBLY AND METHOD OF OPERATIONAL AND	MULTI-ZONB FLANAR HEATER ASSEMBLY AND	MULTI-ZONE PLANAR HEATER ASSEMBLY AND	MELHOD OF OPERATION/Mahawiii MULTI-ZONR PI ANA P HEATER A SERVE	METHOD OF OPERATION/Mahawiii	MULTI-ZONB PLANAR HEATER ASSEMBLY. AND METHOD OR OBER ATTOMACA	MULTI-ZONE FLANAR HEATER ASSEMBLY AND	MULTI-ZONE PLANAR HEATER ASSEMBLY AND	METHOD OF SOLDERING IN A.	CONTROLLED-CONVECTION SURFACE-MOUNT REFLOW, FURNACE/Alley, Carmera, Daley, Roffley	METHOD FOR PRODUCING HIGHLY CONDUCTIVE AND TRANSPAPERT TO SECONDUCTIVE
		AJT.	A H	MESS	ASS MSS	A	<u>A</u>	ATA ASS	AT	MESS	MSS	AJŢ	AT	A	MSS	KSS A	ASS.				MSS
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\$	67392	<u>유</u>	AT	METHOD FOR PRODUCING HIGHLY CONDITIONED				
	·		SS W	AND TRANSPARENT FILMS OF TIN AND FLUORIDE DOPED INDIOM OXIDE BY APCYDARVE	03/12/92	Abandoned	Jegen	
¥.	67392	ZX KR	ATT	METHOD FOR PRODUCING HIGHLY CONDITCTOR				
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		·.	COM	AND TRANSPARENT FILMS OF TIN AND FLUORIDE DOPED INDIUM OXIDE BY APCYDAMME.	02/27/92	Abendoned	Вигоро	
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A	67588		152	PROTECTIVE GAS STREET	05/21/99	D 000		T
	·		MSS	Yuh	09/574,826	6,576,060		
FΑ	67588	3	AJT.	PROTECTIVE GAS SHIELD APPARATUS/Stoddard:	U3/19/U0 09807884 Y	06/10/03		-
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FA	67588	Ç	NESS.	T. C.	2001-7014850 05/19/00		South Korea	- /-
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	67588	TW	AJT . MSS	GAS SHIRLD APPARATUS/Stoddard,	05/19/00		Singapore	
E	67588	B	AJT.		05/19/00		Taiwan	
亞	88579	22	AT.	TECTIVE GAS SHIELD ATTACK	05/19/00		Burape	
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67735	S	ATT	IMPROVED TRENCH ISOLATION PROCESS USING APCVD TEOS; OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWIH/Curie, Req. Kankin	60/127,520 04/02/99	Closed		
67735		AJT MSS	IMPROVED TRENCH ISOLATION PROCESS USING APCVD TEOS: OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/Curis; Rec; Kepkin	09/541,395 03/31/00	6,387,764 Issued: 05/14/02		
67735		AJT. MSS	TRENCH ISOLATION PROCESS USING APCVD TEOS:OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH! Centic Rec; Kaplen	2364975 03/31/00	Abandoned	Cemada	
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67735	KR	AJT	OLATION PROCESS USING APCVD OF TO DEPOSIT A TRENCH FILL OXIDE ODEWALL LINER OXIDATION Carlie Rec. Kenkin	2001-7012564 03/31/00		South Korea	
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		-	N.	TEOS.OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/Cartie Res: Variet	89106191 04/01/00		Triwan
	67735	<u>H</u>	ATT	TRENCH ISOLATION PROCESS USING APCVD TEOS.OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION	00919996.9		
캂	67735	<u>N</u>	AJT	TRENCH ISOLATION PROCESS USING APCVD THOS: OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION	PCI/US00/08650 03/31/00		PCT
	67736	<u> </u>	A-T- MSS VEU	URDWIH! Curit; Rao; Kapkin NEAR-ATMOSPHERIC CVD SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS! Curalheim; Mayor; Monagh; Savage; Vanghan	60/127,532 .04702/99	Closed	
	67736		AJT MESS VED	SEMICONDUCTOR WAFER PROCESS SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Sevage; Memagh; Carvalheirs; Trointic Committer Variabous Memagh; Carvalheirs;	09/483,945 01/13/00	6,610,150 08/26/03	
	67736		ATT		2369042	Abandoned	Cemada
. W.	07736	Ž.	AJT MSS	UCTOR WAFER PROCESSING SYSTEM ICALLY-STACKED PROCESS IAND SINGLE-AXIS DUAL-WAFER SYSTEM/SSYRES; Monegh; Carvalheim;	008006652.3		Chins
•	67736	II.	AJT . MSS	DUCTOR WAFER PROCESSING SYSTEM FICALLY-STACKED PROCESS S AND SINGLE-AXIS DUAL-WAFER SYSTEM/Savage; Monagh; Carvalheim;	145678 A	Abandoned	igraei
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WILLY VERTICALLY STACKED PROCESS CHAMBERS AND SINGEL AXED PROCESS CHAMBERS AND SINGEL AXED DUAL WAFER TRANSPER SYSTEM/Saveg: Menapt: Carvalheira; CHAMBERS AND SINGEL AXED DUAL WAFER TOTALLY STACKED PROCESS CARVALER TOTALLY STACKED PROCESS SYSTEM ANT SIMILONDUCTOR WAFER PROCESS SYSTEM ANT SIMILONDUCTOR WAFER PROCESS SYSTEM ANTENDERS AND SINGEL AXED DUAL WAFER TOTALLY STACKED PROCESS SYSTEM ANTENDERS AND SINGEL AXED DIAL WAFER TOTALLY CONSTRUCTOR WAFER PROCESS SYSTEM ANTENDERS AND SINGEL AXED DIAL WAFER TOTALLY CONSTRUCTOR WAFER PROCESS SYSTEM ANTENDERS AND SINGEL AXED DIAL WAFER TOTALLY CONSTRUCTOR WAFER PROCESS SYSTEM ANTENDERS AND SINGEL AXED DUAL WAFER TOTALLY CONSTRUCTOR WAFER PROCESS SYSTEM ANTENDERS AND SINGEL AXED DUAL WAFER TOTALLY CONSTRUCTOR WAFER PROCESS SYSTEM TOTAL STALLONDUCTOR WAFER PROCESS SYSTEM TOTAL CONSTRUCTOR WAFER PROCESS SYSTEM TOTAL CONSTRU	¥.	67736	Ħ.	A §				
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AJT SEMICONDUCTOR WAFER PROCESS SYSTEM 89106019		•		MESS	Zi .	200105951-8 03/21/00		Singapore
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AJT SEMICONDUCTOR WAFER PROCESS SYSTEM MSS WITH VERTICALLY-STACKED PROCESS TRANSFER STSTEM/Sevage; Menagh; Carvalheira; Troinin; Coesantine; Vanghan; Mayer Troinin; Coesantine; Vanghan; Mayer MSS WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Sevage; Menagh; Carvalheira; O1/13/00 O1/13/00 WITH VERTICALLY-STACKED PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS				K	RICALLY, STACKED PROCESS RS AND SINGLE-AXIS DUAL-WAFER R SYSTEM/Sevage; Menegh; Carvalheim:	3/21/00		Burope
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			MSS	CHAMBERS AND SINGLE AXIS DITAL WATER	Filling Darbo	Inte Date	Foreign
		-		TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troinni; Commine; Vanchan: Mewar	1127/01		
,		· -	A T	SINGLE AXIS DUAL-WAFER TRANSFER	22, 22, 40,7		
		-	VEI	STSTEM/Treinni; Cossentine	04/02/99	Marged into P-67736	98
L	1000	• •	MSS WRSS	METHOD FOR METAL COMPOSITION AND	60/130,783	Closed	
₹ .	68017	-	ATT.	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey;	09/480,730		
FA	21089	প্র	NESS WEEK	CHEMICAL VAPOR DEPOSITION SYSTEMES.	01/06/00	10/27/01	
₽¥.	68017	3	MESS	CHEMICAL VAPOR DEPOSITION SYSTEMBATES	03/03/00	Abindoned	Camada
FA	67017	日	MESS	CHEMICAL VAPOR DEPOSITION SYSTEMBAILER	03/03/00		China
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	68017.	8	MESS	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey;	03/03/00		South Korea
₹.	68017 · TW	1	AJT MSS WEN	CHEMICAL VAPOR DEPOSITION SYSTEMBailey; Michael; Kine	03/03/00 · 89104518		Singapore Taiwan
-	68017	· H	MSS MSS	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey, Michael; Kano	00912173.2.		
-	68017.	2		CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey;	03/03/00 PCI/US00/05/30		ramible
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		•	WEN	APPARATUS/Bartholomew, Yuh, Stumbo, King, Chan	60/134,443	Closed .		T
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F.	88048	3	12	GAS DISTRIBITION COSTS CO.	00/53/60			
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¥.	68048	6	MEN.		05/17/00		uadar.	
			MESS	GAS DISTRIBUTION SYSTEM/Bartholomow; Yuh; Stumbo; King: Chen	2000-0026027		South Korea	
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<u> </u>	680773	- E		Mart. King, Chen.	10/219,924	Abandoned	-	.]
<u>.</u>			MSS	CHEMICAL VAPOR DEPOSITION OF SILICON	08/14/02		•	
	<u> </u>			OLIGOMERS WITH OZONE FOR SUB 0.18 MICRON	07/09/99	Closed		
₹	68073	E	A.	CHEMICAL VAPOR DRPOSTITION OF ATT VALID		•		•
	•		SC S	DIOXIDE BY USING ALKYLSHOXANE OLIGOMERS WITH OZONE FOR SUB 0.18 MCRON	09/542,612 04/04/00	6465044		<u> </u>
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			SSING	MERS	00811030.1		China	
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			CO	MERS	2001-509075 06/15/00		Tapen	
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			MSS	OXIDE FILMS USING ALCYLSHOXANE OLIGOMERS WITH OZONE	89113435 07/06/00	153183	Taiwan	
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	·		. SSW	INORGANICIORGANIC DIELECTRIC FILMS/Lopats;	Filing Date 11/19/99	Istue Date	Countries	T
∢			ATE	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIST. ECTRIC FILMS/Lopata; Febts	09/715,455 11/17/00			
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			AJT.	CHEMICAL VAPOR DEPOSITION APPARATUS/Cambell: Miller	06/412,237	4.545.327		
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∢	768897	6	1	CHEMICAL VAPOR DEPOSITION WARED BOAM	Filing Date	Isine Date	Countries	
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		•	CCPA	Learn; DaBois	12/05/85	4,641,604		7-
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	:		MESS	Learn; DuBois	06/828,625	4,694,778		<u>,</u>
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Title/Inventors	RECIRCULATING HEATER HYBAITET COCT THE	SYSTEM/Bolton; Wiesen	RECIRCULATING HEATER/Boltom-Witnern	SEMICONDUCTOR THERMAL PROCESSOR RECIRCAL ATING HEATER D. T.	SEMICONDUCTOR THERMAL PROCESSOR RECTROTT ATMG TED ATTER IN	SEMICONDUCTOR THERMAL PROCESSOR RECTROTT ATTWO HEATERMAN	SEMICONDUCTOR THERMAL PROCESSOR RECTROTT ATTACK THE ATT	SEMICONDUCTOR THERMAL PROCESSOR PROPERTY ATTENDED	DOUBLE WALL REACTION CHANGED	GLASSW.	DOUBLE WALL REACTION CHAMBER GLASSWARE/Fowler Parth: Vocasiti: 117	DOUBLE WALL REACTION CHAMBER	DOUBLE WALL REACTION CHAMBER	DOUBLE WALL REACTION CHAMBER	GLASSWARR/Fowler, Parvin; Kowalaki; Wiesen	GLASSWARE/FOWLET PATYIN: Kounlist: Witness	DOUBLE WALL REACTION CHAMBER GLASSWARER P. P. C.	LINEAR RPT REACTOR/Kowalski; Radiff; Suh: Oin	HOT WALL RAPID THERMAL PROGRESSION IN THE		
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∢	88005	<u></u>	AJT MSS ·	HOT WALL RAPID THERMAL PROCESSOR/Radiff,	07/07/00 09/638.113	6.459.310	
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FA 68916 1-SG AJT MODULAR FLUID DELIVERY AFPARATUSNguyen 20201201-1	FA	91689	_	ATT	-	03/06/02 P7:00:00747		South Korea	
FA 68916 1-TW AJT MODULAR FLUID DELIVERY APPARATUS/NETW 91103478 91202472 91202473	FA	91689	_	ACT.	R FLUID DELIVERY APPARATUS/Ngryen	03/01/02		Malayan	T
FE 68916 1-EP AJT MODULAR FLUID DELIVERY. APPARATUSNIGUY 0222602.	FA	68916		ATT	R FLUID DELIVERY. APPARATUS/Ngryen	02/27/02		Singapore	
69013 MSS FLUOROPOLYMER INTERLAYER DIRECTRIC BY CAPOR DEPOSITION/Rose; Bichlo; 05/04/01 (filed by Lopert; Mocella, MSS DEPOSITION/Rose; Bichlo; Der Pom) Der Pom)	毘	91689	_	AJT	RELUID DELIVERY, APPARATUS/Nguyen	02/26/02 02/26/02		Taiwan	
CHRMICAL VAPOR DEPOSITION/Rose; Brichlory Loputs, Mocella	Д	69013		MSS	OLYMER INTERLAYER DIRIECTED BY	03/06/02	·	Ваторе	γ
Cold AJT DEPOSITION OF FLUOROPOLYMER FILMS/Mocells: Dar Pont) Dar Pont					POR DEPOSITION Rose; Brichlo;	05/04/01 (filed by		Co-owned wift.	
G9173 MSS MODEL BASED TEMPERATURE CONTROL OF Unfiled	∢	69013		AJT MSS ·	N OF FLUOROPOLYMER FILMS/Mocella;		mfled	The state of the s	
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69174 1 MSS IN-SITU SENSING AND ENDPOINT DETECTION IN 60258,931 Closed COPPER CAP/Sale; Laj; Oh MSS POINT DETECTION IN CHEMICAL MECHANICAL POLISHING/Sale; Laj; Oh 1221/01	₹ .	69174			THOD AND APPARATUS FOR END ECTION IN CHEMICAL MECHANICAL		#16,921	Course	
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•	71514	<u> </u>	MSS	METHOD OF DEPOSITING AN OXIDE FILM BY				
	71517	_		new;	05/20/03/	•	Taiwan	
		ટું .	N N	METHOD OF DEPOSITING AN OXIDE FILM BY CHEMICAL VAPOR DEPOSITION/ Parts Bartholomew;	05/20/03		PCF	
	71664		Ness.	D METEOD FOR HYDROGEN BICE	•		:	-
	1204		,		06/06/02	Closed	. .	_
	71564		MSS	D METHOD FOR HYDROGEN TO				
 -∤`					10/456,850 06/06/03			_
	\$	MY	MESS	1		·, .		_
- ``	71564	M.	MSS		06/06/03		Malaysia	
	·			FOR HYDROGEN RICH Herring: Porter; Dodwell;		. .	Taiwan	
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• •	Pattent No./	Large Date		Closed							Closed			Closed		Closed				
	Sertal No./			£ 60/399,463			_	07/29/03 -			60/396,536 07/15/02			11/22/02		06/23/02	·	06/23/03 .	PCT/0303/19982 06/23/03	,
Titlesinventure		STEED AND METHOD FOR HYDROGEN RICH	OZONE OXIDATION OF SITT CONTROL	FORMATION OF AN INTERPACIAL LAYER FOR HIGH-L GATH STATES FOR	OZONE OXIDATION OF SILICON SUBSTRATES FOR	HIGH-E GATE STACKS/Sonzaki: Horing	FORMATION OF AN INTERPACTATION SUBSTRATES FOR	OZONB OXIDATION OR STITCON CONTROL	FORMATION OF AN INTERFACIAL LAYER FOR	OPTIMIZED MINI-BATCH CONFIGURATIVE	VERTICAL CHAMBER/Qui; Wildman; Colling: Kownist; Edwards; DuBois; Nam; Toxkaman; Mr. Strange		VHPTICAT OF THE BATCH CONFIGURABLE	Colling, Kownlett, Edwards; DaBoie; Nam; Torkaman;	SYSTEM AND METHOD FOR ATOMICT AVER	METHOD AND SYSTEM FOR ATOMIC! A VERN	SYSTEM AND METHOD FOR ATOMOST ATTEMPT	I AND REMOVAL/Kapida; Sang-la Lee D. METHOD ROP A TOLICO		HE DEPOSITED.
	. IARG		. MESS	-	MSS .	. 700	· 2	MSS		MESS			MESS .		MSS	MSS		MSS	MSS	
Se No.	71564 PC		71581		71581	71581 PC		WT 18217	·	71582		- 100 E	<u></u>	·	8	8	7. T.W.	PC PC	6 11	
Reference No.	臣		4		<u>₹</u>	FP 71		FA 77				A			P 71606	A 71606	PA 71606	FP 71606	P 71606	- Constant

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Reference No.	.đ,	•	TitleInvanture			
				Serial No.	Patient No.	The state of the s
71606	MI-I	NESS	METHOD AND SYSTEM FOR PHOTO-ASSISTED	Filing Date	Istus Date.	Countries
.				06/23/03		Taiwan
71606	24	MSS	AND SYSTEM FOR PHOTO-ASSISTED AYER DEPOSITION AND PER CONT.			1
71622		MSS		06/23/03		2
71622		MSS	ED COMPONENTS/Serralt; Seng-in Legal LAYER DEPOSITION OF THIN FILMS	60/397,029 07/18/02	Closed	
71622	TW.	MSS	WITH MIXED COMPONENTS/Sonzeld; Song-in Loc MOLECULAR LAYER DEPOSITION OF THIN HIT AS			
71622	2	MESS	AR LAYER DEPOSITION OF THIN RELYS	07/16/03		Taiwan
71637		MSS		35	Closed	PCT
71638		MSS	OF HIGH-k	2	Closed	
71638		MSS		07/19/02		
71638	È	MSS		07/17/03		
	2	MSS	YER DEPOSITION OF HIGH-E	•		1 stwan
71639	A	MSS	OF GATE	07/19/03 .		FCI
71639 T	TW X	MSS				
4 68917	PCT .	SSW	LOW TEMPERATURE OZONE ANNEAL OF GATE	07/17/03		Taiwan
1	1	7	CHARLECTRICS/Sentable, Sing-in Los 07/1	50/91		PCT

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1	Reference No.	_			· · ·	:	•	
				Title/Inventors	Sectal No.	Percent		
<u>A</u>	71640		SSEV	LOW TEMPERATURE DIELECTRIC DEPOSITION	Filling Date	Intra Date	Foreign Countries	1.
FA.	71640	AL.	MESS	PERATURE DIELECTRIC DEPOSITION	07/19/02	Dagger		
£	71640	2	MSS	PHRATURE DISTRICT DEPOSITION	07/17/03		Taiwan	,
e.	71641	÷	MSS	HF-O-	07/15/03 60/396,744 07/19/07	Closed	p.	
¥	71641		MESS	ATOMIC LAYER DEPOSITION OF HF-O-				
FA	71641	<u>A</u>	MSS	HR-O-	92119583		Taiwan	
£:		2	MSS	RITION OF HE-C.	07/16/03	'	PCT	
	71642		MSS	V.ASSISTED ATOMIC LAYER N/Senzalt; Supe-In Lee	2	Closed combined		
Α .	71643		MSS	TION FOR THE FORMATION OF D CAPACITOR DISLECTRIC WITH SCTRICAL PROPERTY.		with 71606-1 Closed		· · ·
FA	71643 T	A.	SSP	TION FOR THE FORMATION OF CAPACITOR DICAPACITOR DICECTRIC WITH SCHOLES OF THE SCHOOL WITH STRUCKLES OF THE SCHOLES OF THE SCHO	07/17/073		Taiwan	
-	71643 PC		MSS		07/17/03		PCT	
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å	D. Contraction						-
		٠,		Title/fuventor-			
ļ					Sertal No.	Patent No.	
<u>.</u>	444	·	MSS	IN-SITU FORMATION OF MIM CAPACITORS/Sang-in	Filling Date 60/396.734	June Date	Foreign
FA.	71644	Ž.	MSS	IN-SITU FORMATION OF MIM CAPACITURES.	07/19/02		
	71644	2	SSOM		07/17/03		Taiwan
P.	71645		SSPA		07/17/03		PCT.
¥	71645	•	MSS		07/19/02 Closed combined	Closed, combined with 71638	
<u>.</u>	71663		MSS	DE MAKENG METAL CAPS FOR	with 71638 60/397,031		
V	71653		VESS	FOR	07/18/02 ·		
A.	71720		MSS	1	60/404,372 08/18/72	Closed	: .
Α .	71720		MESS	ATOMIC LAYER DEPOSITION OF HIGH-K METAL OXIDES FOR GATE AND CAPACITOR			
FA 7	WT 02717		WBS.		08/14/03		
FP .	71720 PC		MSS	H	08/18/03		
F	חשו	Z	MSS		2	Closed	
	1	1		DIRECTRICS/Sang-in Loc. S.K. Loc. Shin; Searshi	•.		

		The County		•	Taiwan	•	PCT	· .					Taiwan		PCF			•	• .	-		· .	
I.	Pattentino	Icrae Daite	_			•		•	Closed								Closed				•		
	Sertal No.	Filling Date		:	08/14/03		08/18/03		60/404,363 08/18/02		• .		08/14/03		08/18/03		60/408,709	•		50/50/60	•		Closed, combined with 71730
Title/Inventors		ATOMIC LAYER DEPOSITION OF MEETIN	SILICATES FOR HIGH-K GAIE AND CAPACITOR DIELECTRICS/SOR-In Low 8 V 1	ATOMIC LAYER DEPOSITION OF A SECOND		ATOMIC LAYER DEPOSITION OF METAT	SILICATES FOR HIGH-K GATE AND CAPACITOR	LOW TEMPERATURE DEPOSITION OF OUR	OXIDES AND SILICON OXYNITRIDE/Sang-In Lee; Skin: Some Li	LOW TEMPERATURE DEPOSITION OF SET ICON	S.K. Lee, Shir, Sarrah	LOW TEMPERATURE DEPOSITION OF THE	OXIDES AND SILICON OXYNITRIDE/Sang-In Loc;	LOW TEMPERATURE DEPOSITION OR STITION	S.K. Lee, Ship. Sericon Oxynitride/Sang-In Lee;	LOW TEMPERATURE DEPOSITION OF SET	BASED THIN FILES BY SINGLE WATER HOT-	DEPOSITION (RTCVD)/Senzaki; Butili: Tressel.	LOW. TEMPERATURE DEPOSITION OF SIT ICON	WALL RAPID THERMAL CHEMICAL	DEPOSITION (RCTCVD)/Senzaki; Barelli; Teasdale		WALL RAPID THERMAL CHEMICAL VAPOR
		SSW	•	MSS		MESS		MSS		. MSS	·	MSSS		NESS		MESS			MSS			MSS	•
Reference No.	11211	17,11		WT 12217	· ·	71721 PC		mm2		7777		1172 TW		7 22 K		71730	•	71.730	2			4	•

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FA	गारा	TW	MESS	VACUUM ASSEMBLY WITH MILTING TAKES	Filling Date	Into Date	Portign Countries
£	71751	2	MSSS	SEQUENCE/Qui	07/10/03		Taiwan
				SEQUENCE ON	07/10/m3		PCT.
	11.752		WEN	COILING COOLING SYSTEM AND METHOD/Qui;			
	71752	TW.	MSS	CYCLONIC COOLING SYSTEM AND METHOD/Qui; Colins	270		Taiwan
E:		2	MES	CYCLONIC COOLING SYSTEM AND METHOD/Qui; Collins	07/1003		PCT
Ý.	71753		MSS	COOLING SYSTEM AND METHOD/Qui; Collins	Closed, combined		
A	71754		MSS	FHED FORWARD TEMPERATURE CONTROLLER/MA	with 71.752 ·		•
A	22717		MSS	ALIGNMENT APPARATUS AND METHOD OF ALIGNING A WAFER MA	Closed		
A .	71756		MSS.	CATION PROTOCOL AND METHOD OF ROBOT THROITCHPITTAL	ėn pold		
A 7	72717		MSS	DISTRIBUTED SINGLE WIRE NETWORKING REEVATOR CONTROL			
FA 7	T 727.T	₩.	MSS	OR CONTROL SYSTEM & METHODIMA DUCTOR MANUFACTURING	07/10/03		Thivan
RP 7		<u>ک</u>	MSS	THOD IN	07/10/03.		Ţ,
	71758.	AM	MSS	LOAD PORT, Jeffay B. Kowalski			
PA 71	WT 82117		MSS	LOAD PORT APPARATUS; Jeffery B. Kowaleki 07,	07/15/03		T. Aritonan
1935AAE	F71935/MSS (463(335-878)	25.25					
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PC MSS LOAD POR	LOAD PC	LOAD POR	RT APPARATUS; Jeffery B. Kowalski	Filting Date	Issue Date	Countries
MSS THERMAL ENVECONS METHOD:		THERMAL BNVIRONA METHOD:	THERMAL PROCESSING CHAMBER HIVTRONMENTAL CONTROL SYSTEM AND METHOD: Alm String			5
TW MSS CONTROL C WAFER LOA	· · CONTRO! WAFER L	CONTROL C	CONTROL OF A GASEOUS ENVIRONMENT IN A WAFER LOADING CHAMBER; Alen Stemer	07/15/03		Triwan
PC MISS CONTROL C WAFER LOA	CONTROI WAFER L	CONTROL C	OF A GASEOUS ENVIRONMENT IN A OADING CEAMBER; Alen Stemer	07/15/03		PCT
MSS METBOD AN WEN HEATING OF		METHOD AN HEATING OF	AND SYSTEM FOR ISOTHERMAL OF WAFERS; Jeffey Kowalski	Closed, combined		
MGSS		HEATER H.E TEMPERATU	HEATER HEMENT SELECTABLE FOR VARIABLE TEMPERATURE PROCESSING/Qui			•••
TW MSS VARIABLE HE TEMPERATUR	VARIABLE	VARIABLE HE TEMPERATUR		07/10/03		Taiwan
PC MSS VARIABLE HEATER ELEMEN TEMPERATURE RANGES/Qia	VARIABLE	VARIABLE HE TEMPERATUR	T FOR LOW TO HIGH	07/10/03		PCT
MSS T-RAIL SUPPO		T-RAIL SUPPOI	PPORT/DaBois			
TW MSS METHOD & AL	METHOD & SEMICOND		APPARATUS FOR SUPPORTING UCTOR WAFFRSOn Bail	07/10/93		Toimes
PC MSS METHOD & A SEARCONDUC	METHOD & SEMICOND	METHOD & A	ORTING	07/10/03		Į.
MSS FEED FORWA METHOD/Took A-71754)	FEED FORN METEODAL A-71754)	FRED FORWA METHOD/Tork A-71754)	/ARD CONTROL SYSTEM AND advances; Redliff (This case may be related to			
MES SYSTEM ARC	SYSTEM AR	SYSTEM ARC	SYSTEM ARCHITECTURE AND METHOD FOR SEMICONDICTOR BARDITATIONS			
			CACAL FARMICATION/Holms; Wisson		'a	

1	Heference No.	ور				•		
ľ				Title/Inventors	Serfal No./	Patent No.	Berte	ı
	71824		MES	REMOTE PLASMA NITRIDATION OF HIGHER CAST	Filing Date	Icens Date	Countries	
				DIRLECTRICS/Senzald; Bercaw; Chaffarn; Hignohi;	11/08/02		ć.	
	71824		MSS	REMOTE PLASMA NITRIDATION OF HIGH-K GATE				
- [71884		997					
			E H	METHOD OR ATOMIC LAYER REMOVAL OR BERACHINGSong-in Los	Closed, combined .			
	72081	A.	MSS	TRANSPORT SYSTEM HAVING SHARED LOAD. LOCK FRONT-END ASSEMBLY FOR TRANSFER OF MEDIA IN A CONTRO! I EN ENTER OF	60/443,969 01/31/03			′
	72138		MSS	RUBCTRODE STRUCTURE AND METHOD OF PABRICATING AN ELECTRODE HAVING LOW TEMPERATURE OXIDE FILM; S.I. Lee, Y. Senzah			Client Ref. No D-7031	
	72218	X	MSS	NENT	60/464,458		Cleat Rof No.	
	78.		* 10 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	ADDRES MALE GAS DELLYERY MANIFOLD;	a	And the desired that the second of the secon		- T
	72332	A .	MSS	BANING OF COPPER DETECTION	DSS GROS		D-2493	
``	72333	2 .	MSS .	METHOD OF REDUCING CONTACT RESISTANCE OF COPPER INTERCONNECT				
	72344	·	MSS	BATCH FURNACE WAFER RADIAL DELTA TEMPERATURE CONTROL USING A BOTTOM AND TOP HEATER				-
	72345	SEM		SEMICONDUCTOR VERTICAL FURNACE HALO RING CONCEPT; D. DuBois, C. Porter, M. Mogand				-
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Serial No./	
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No.	Reference M

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"A" denotes US a patent/patent application/invention disclosure "PA" "FP" and "FB" denote a. foreign patent/patent amiliesti-